

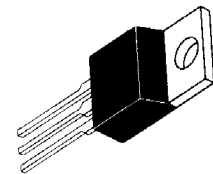
Silicon Controlled Rectifiers Reverse Blocking Triode Thyristors

... designed for industrial and consumer applications such as temperature, light and speed control; process and remote controls; warning systems; capacitive discharge circuits and MPU interface.

- Center Gate Geometry for Uniform Current Density
- All Diffused and Glass-Passivated Junctions for Parameter Uniformity and Stability
- Small, Rugged Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Low Trigger Currents, 200 μ A Maximum for Direct Driving from Integrated Circuits

MCR72 Series

SCRs
 8 AMPERES RMS
 50 thru 800 VOLTS



(TO-220AB)

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted.)

Rating	Symbol	Value	Unit
Peak Repetitive Forward and Reverse Blocking Voltage ⁽¹⁾ ($T_J = -40$ to 110°C , 1/2 Sine Wave, $R_{GK} = 1\text{k}\Omega$)	V_{DRM} or V_{RRM}	50 100 200 400 600 800	Volts
On-State RMS Current ($T_C = 83^\circ\text{C}$)	$I_T(\text{RMS})$	8	Amps
Peak Non-repetitive Surge Current (1/2 Cycle, 60 Hz, $T_J = -40$ to 110°C)	I_{TSM}	100	Amps
Circuit Fusing ($t = 8.3$ ms)	i^2t	40	A^2s
Peak Gate Voltage ($t \leq 10$ μs)	V_{GM}	± 5	Volts
Peak Gate Current ($t \leq 10$ μs)	I_{GM}	1	Amp
Peak Gate Power ($t \leq 10$ μs)	P_{GM}	5	Watts
Average Gate Power	$P_{G(AV)}$	0.75	Watts
Operating Junction Temperature Range	T_J	-40 to +110	$^\circ\text{C}$

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



MCR72 Series

MAXIMUM RATINGS — continued

Rating	Symbol	Value	Unit
Storage Temperature Range	T_{stg}	-40 to + 150	°C
Mounting Torque	—	8	in. lb.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.2	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	°C/W

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$, $R_{GK} = 1\text{ k}\Omega$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Peak Forward or Reverse Blocking Current ⁽¹⁾ ($V_{AK} = \text{Rated } V_{DRM} \text{ or } V_{RRM}$) $T_J = 25^\circ\text{C}$ $T_J = 110^\circ\text{C}$	I_{DRM} , I_{RRM}	— —	— —	10 500	μA μA
On-State Voltage ($I_{TM} = 16\text{ A Peak}$, Pulse Width $\leq 1\text{ ms}$, Duty Cycle $\leq 2\%$)	V_{TM}	—	1.7	2	Volts
Gate Trigger Current (Continuous dc) ⁽²⁾ ($V_D = 12\text{ V}$, $R_L = 100\ \Omega$)	I_{GT}	—	30	200	μA
Gate Trigger Voltage (Continuous dc) ($V_D = 12\text{ V}$, $R_L = 100\ \Omega$) ($V_D = \text{Rated } V_{DRM}$, $R_L = 10\text{ k}\Omega$, $T_J = 110^\circ\text{C}$)	V_{GT}	— 0.1	0.5 —	1.5 —	Volts
Holding Current ($V_D = 12\text{ V}$, $I_{TM} = 100\text{ mA}$)	I_H	—	—	6	mA
Critical Rate-of-Rise of Forward Blocking Voltage ($V_D = \text{Rated } V_{DRM}$, $T_J = 110^\circ\text{C}$, Exponential Waveform)	dv/dt	—	10	—	$\text{V}/\mu\text{s}$
Gate Controlled Turn-On Time ($V_D = \text{Rated } V_{DRM}$, $I_{TM} = 16\text{ A}$, $I_G = 2\text{ mA}$)	t_{gt}	—	1	—	μs

1. Ratings apply for negative gate voltage or $R_{GK} = 1\text{ k}\Omega$. Devices shall not have a positive gate voltage concurrently with a negative voltage on the anode. Devices should not be tested with a constant current source for forward and reverse blocking capability such that the voltage applied exceeds the rated blocking voltage.
2. Does not include R_{GK} current.